Microsemi Corporation - M1AGLE3000V2-FG896 Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	75264
Total RAM Bits	516096
Number of I/O	620
Number of Gates	3000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	896-BGA
Supplier Device Package	896-FBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1agle3000v2-fg896

IGLOOe Ordering Information

AGLE3000 V2 – FG G 896 Y I

Application (Temperature Range)
- Blank = Commercial (0°C to +70°C Ambient Temperature)
- I = Industrial (–40°C to +85°C Ambient Temperature)
- PP = Pre-Production
- ES = Engineering Sample (Room Temperature Only)

Security Feature
- Y = Device Includes License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio
- Blank = Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio

Package Lead Count

Lead-Free Packaging
- Blank = Standard Packaging
- G = RoHS-Compliant Packaging

Package Type
- FG = Fine Pitch Ball Grid Array (1.0 mm pitch)

Supply Voltage
- 2 = 1.2 V to 1.5 V
- 5 = 1.5 V only

Part Number

IGLOOe Devices
- AGLE600 = 600,000 System Gates
- AGLE3000 = 3,000,000 System Gates

IGLOOe Devices with Cortex-M1
- M1AGLE3000 = 3,000,000 System Gates

Note: Marking Information: IGLOO V2 devices do not have V2 marking, but IGLOO V5 devices are marked accordingly.

Flash Advantages

Low Power

Flash-based IGLOOe devices exhibit power characteristics similar to those of an ASIC, making them an ideal choice for power-sensitive applications. IGLOOe devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

IGLOOe devices also have low dynamic power consumption to further maximize power savings; power is even further reduced by the use of a 1.2 V core voltage.

Low dynamic power consumption, combined with low static power consumption and Flash*Freeze technology, gives the IGLOOe device the lowest total system power offered by any FPGA.

Security

The nonvolatile, flash-based IGLOOe devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. IGLOOe devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

IGLOOe devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of protection in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in IGLOOe devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. AES was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. IGLOOe devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. IGLOOe devices with AES-based security provide a high level of protection for remote field updates over public networks such as the Internet, and are designed to ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of the IGLOOe family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The IGLOOe family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. An IGLOOe device provides the best available security for programmable logic designs.

Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based IGLOOe FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Flash-based IGLOOe devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based IGLOOe devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs. In addition, glitches and brownouts in system power will not corrupt the IGLOOe device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based IGLOOe devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

Table 2-3 • **Flash Programming Limits – Retention, Storage, and Operating Temperature[1]**

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T_{STG} (°C) [2]	Maximum Operating Junction Temperature T_J (°C) [2]
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

1. *This is a stress rating only; functional operation at any condition other than those indicated is not implied.*
2. *These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 for device operating conditions and absolute limits.*

Table 2-4 • **Overshoot and Undershoot Limits [1, 3]**

VCCI	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle[2]	Maximum Overshoot/ Undershoot[2]
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. *Based on reliability requirements at junction temperature at 85°C.*
2. *The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.*
3. *This table does not provide PCI overshoot/undershoot limits.*

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every IGLOOe device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-1 on page 2-4 and Figure 2-2 on page 2-5.

There are five regions to consider during power-up.

IGLOOe I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points (Figure 2-1 on page 2-4 and Figure 2-2 on page 2-5).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI **Trip Point:**
Ramping up: 0.6 V < trip_point_up < 1.2 V
Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC **Trip Point:**
Ramping up: 0.6 V < trip_point_up < 1.1 V
Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.

- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper powerup behavior. Power ramp-up should be monotonic at least until VCC and VCCPLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V ± 0.25 V), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *IGLOOe FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

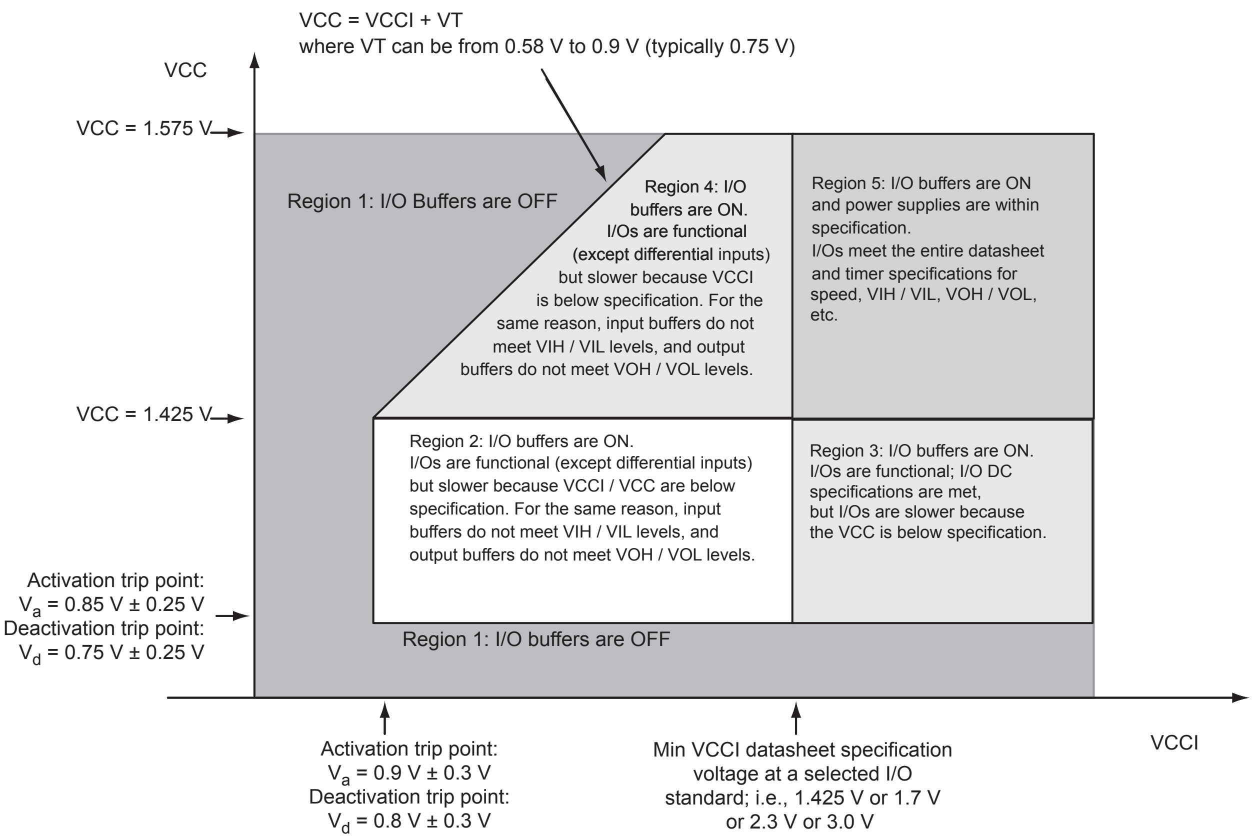

Figure 2-1 • **V5 – I/O State as a Function of VCCI and VCC Voltage Levels**

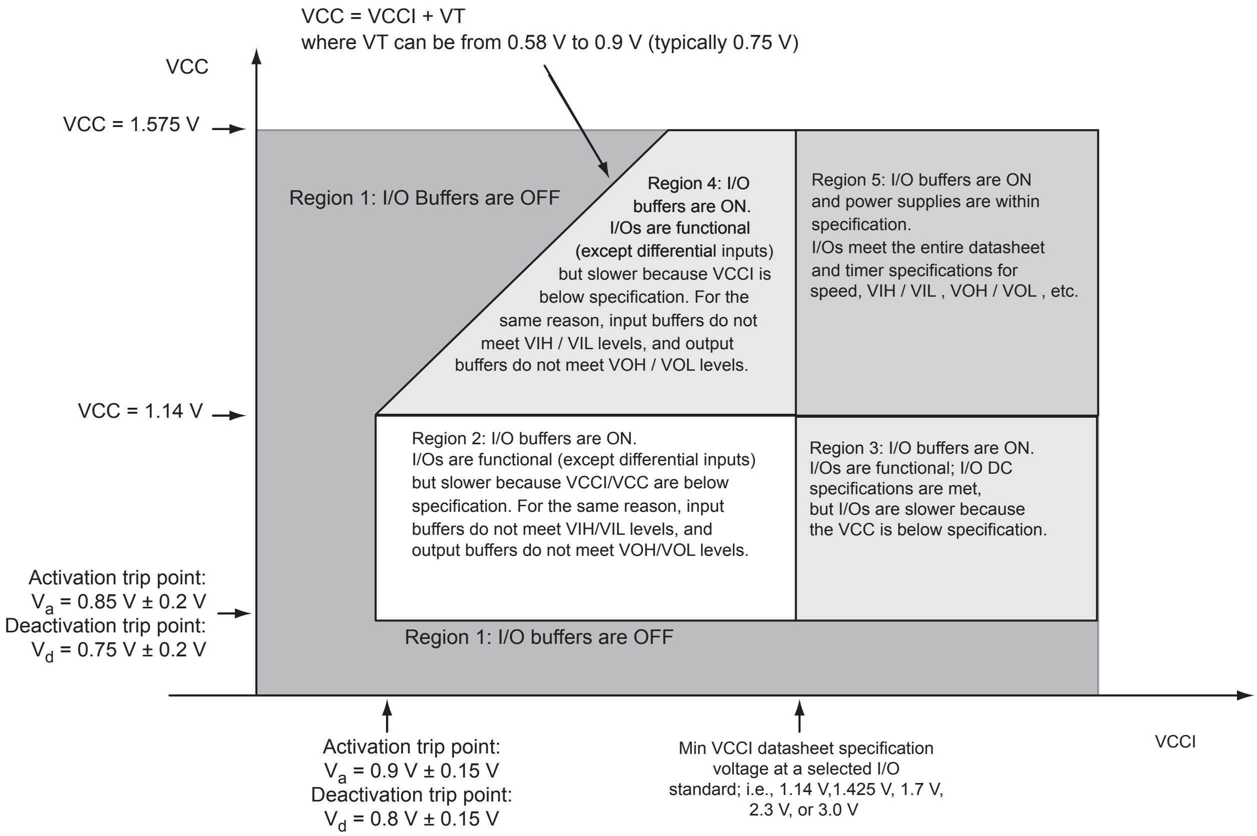

Figure 2-2 • **V2 Devices – I/O State as a Function of VCCI and VCC Voltage Levels**

Thermal Characteristics

Introduction

The temperature variable in Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ 1 can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A$$

EQ 1

where:

T_A = Ambient Temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in Table 2-5.

P = Power dissipation

Power Consumption of Various Internal Resources

Table 2-15 • **Different Components Contributing to the Dynamic Power Consumption in IGLOOe Devices For IGLOOe V2 or V5 Devices, 1.5 V DC Core Supply Voltage**

Parameter	Definition	Device-Specific Dynamic Contributions (µW/MHz)	
		AGLE600	AGLE3000
PAC1	Clock contribution of a Global Rib	19.7	12.77
PAC2	Clock contribution of a Global Spine	4.16	1.85
PAC3	Clock contribution of a VersaTile row	0.88	
PAC4	Clock contribution of a VersaTile used as a sequential module	0.11	
PAC5	First contribution of a VersaTile used as a sequential module	0.057	
PAC6	Second contribution of a VersaTile used as a sequential module	0.207	
PAC7	Contribution of a VersaTile used as a combinatorial module	0.207	
PAC8	Average contribution of a routing net	0.7	
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-9.	
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-14 on page 2-10.	
PAC11	Average contribution of a RAM block during a read operation	25.00	
PAC12	Average contribution of a RAM block during a write operation	30.00	
PAC13	Dynamic contribution for PLL	2.70	

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power calculator or SmartPower in Libero SoC software.

Table 2-16 • **Different Components Contributing to the Static Power Consumption in IGLOO Devices For IGLOOe V2 or V5 Devices, 1.5 V DC Core Supply Voltage**

Parameter	Definition	Device Specific Static Power (mW)	
		AGLE600	AGLE3000
PDC1	Array static power in Active mode	See Table 2-12 on page 2-8.	
PDC2	Array static power in Static (Idle) mode	See Table 2-11 on page 2-7.	
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7.	
PDC4	Static PLL contribution	1.84	
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-12 on page 2-8.	
PDC6	I/O input pin static power (standard-dependent)	See Table 2-13 on page 2-9.	
PDC7	I/O output pin static power (standard-dependent)	See Table 2-14 on page 2-10.	

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in the Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-19 on page 2-15.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-20 on page 2-15.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-20 on page 2-15. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

P_{STAT} = (PDC1 or PDC2 or PDC3) + N_{BANKS} * PDC5 + N_{INPUTS}* PDC6 + $N_{OUTPUTS}$* P_{DC7}

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

N_{BANKS} is the number of I/O banks powered in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + $N_{S\text{-}CELL}$ * PAC4) * F_{CLK}

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *IGLOOe FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *IGLOOe FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution—$P_{S\text{-}CELL}$

$P_{S\text{-}CELL} = N_{S\text{-}CELL}$ * (PAC5 + α_1 / 2 * PAC6) * F_{CLK}

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-19 on page 2-15.

F_{CLK} is the global clock signal frequency.

Combinatorial Cells Contribution—P_{C-CELL}

$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * PAC7 * F_{CLK}$

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-19 on page 2-15.

F_{CLK} is the global clock signal frequency.

Routing Net Contribution—P_{NET}

$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * PAC8 * F_{CLK}$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-19 on page 2-15.

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution—P_{INPUTS}

$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * PAC9 * F_{CLK}$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-19 on page 2-15.

F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution—$P_{OUTPUTS}$

$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * PAC10 * F_{CLK}$

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-19 on page 2-15.

β_1 is the I/O buffer enable rate—guidelines are provided in Table 2-20 on page 2-15.

F_{CLK} is the global clock signal frequency.

RAM Contribution—P_{MEMORY}

$P_{MEMORY} = PAC11 * N_{BLOCKS} * F_{READ-CLOCK} * \beta_2 + PAC12 * N_{BLOCK} * F_{WRITE-CLOCK} * \beta_3$

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{READ-CLOCK}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations—guidelines are provided in Table 2-20 on page 2-15.

$F_{WRITE-CLOCK}$ is the memory write clock frequency.

β_3 is the RAM enable rate for write operations—guidelines are provided in Table 2-20 on page 2-15.

PLL Contribution—P_{PLL}

$P_{PLL} = PDC4 + PAC13 * F_{CLKOUT}$

F_{CLKOUT} is the output clock frequency.[1]

1. *If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ($P_{AC13} * F_{CLKOUT}$ product) to the total PLL contribution.*

1.2 V DC Core Voltage

Table 2-44 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	1.55	8.14	0.26	1.66	2.14	1.10	8.14	6.46	3.80	3.79	13.93	12.25	ns
100 µA	8 mA	Std.	1.55	6.68	0.26	1.66	2.14	1.10	6.68	5.57	4.25	4.69	12.47	11.36	ns
100 µA	12 mA	Std.	1.55	5.65	0.26	1.66	2.14	1.10	5.65	4.91	4.55	5.25	11.44	10.69	ns
100 µA	16 mA	Std.	1.55	5.36	0.26	1.66	2.14	1.10	5.36	4.76	4.61	5.41	11.14	10.55	ns
100 µA	24 mA	Std.	1.55	5.20	0.26	1.66	2.14	1.10	5.20	4.78	4.69	6.00	10.99	10.56	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.*

Table 2-45 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	1.55	4.65	0.26	1.66	2.14	110	4.65	3.64	3.80	4.00	10.44	9.43	ns
100 µA	8 mA	Std.	1.55	3.85	0.26	1.66	2.14	1.10	3.85	2.99	4.25	4.91	9.64	8.77	ns
100 µA	12 mA	Std.	1.55	3.40	0.26	1.66	2.14	1.10	3.40	2.68	4.55	5.49	9.19	8.46	ns
100 µA	16 mA	Std.	1.55	3.33	0.26	1.66	2.14	1.10	3.33	2.62	4.62	5.65	9.11	8.41	ns
100 µA	24 mA	Std.	1.55	3.36	0.26	1.66	2.14	1.10	3.36	2.54	4.71	6.24	9.15	8.32	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.*
3. *Software default selection highlighted in gray.*

1.2 V LVCMOS (JESD8-12A)

Low-Voltage CMOS for 1.2 V complies with the LVCMOS standard JESD8-12A for general purpose 1.2 V applications. It uses a 1.2 V input buffer and a push-pull output buffer.

Table 2-64 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

1.2 V LVCMOS[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[2]	IIH[3]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[4]	Max. mA[4]	µA[5]	µA[5]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. *Applicable to V2 devices ONLY.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
4. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

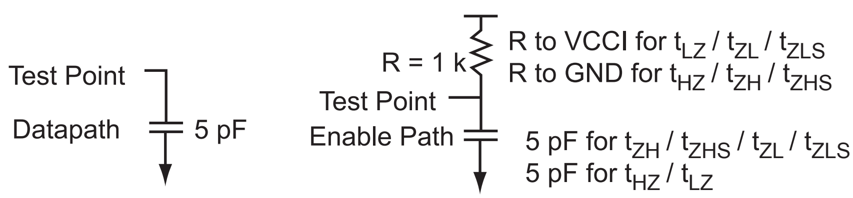

Figure 2-11 • AC Loading

Table 2-65 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	1.2	0.6	–	5

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-23 for a complete table of trip points.

SSTL3 Class I

Stub-Speed Terminated Logic for 3.3 V memory bus standard (JESD8-8). IGLOOe devices support Class I. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-105 • Minimum and Maximum DC Input and Output Levels

SSTL3 Class I	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	μA[4]	μA[4]
14 mA	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.7	VCCI – 1.1	14	14	51	54	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operating conditions where –0.3 V < VIN < VIL.
2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.

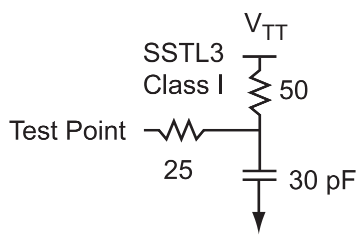

Figure 2-21 • AC Loading

Table 2-106 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.5	1.5	1.485	30

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-23 for a complete table of trip points.

Timing Characteristics

1.5 V DC Core Voltage

**Table 2-107 • SSTL 3 Class I – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 3.0 V VREF = 1.5 V**

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.98	2.05	0.19	1.09	0.67	2.09	1.71			5.72	5.34	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

**Table 2-108 • SSTL 3 Class I – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V,
Worst-Case VCCI = 3.0 V VREF = 1.5 V**

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	1.55	2.32	0.26	1.32	1.10	2.37	2.02			8.17	7.83	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

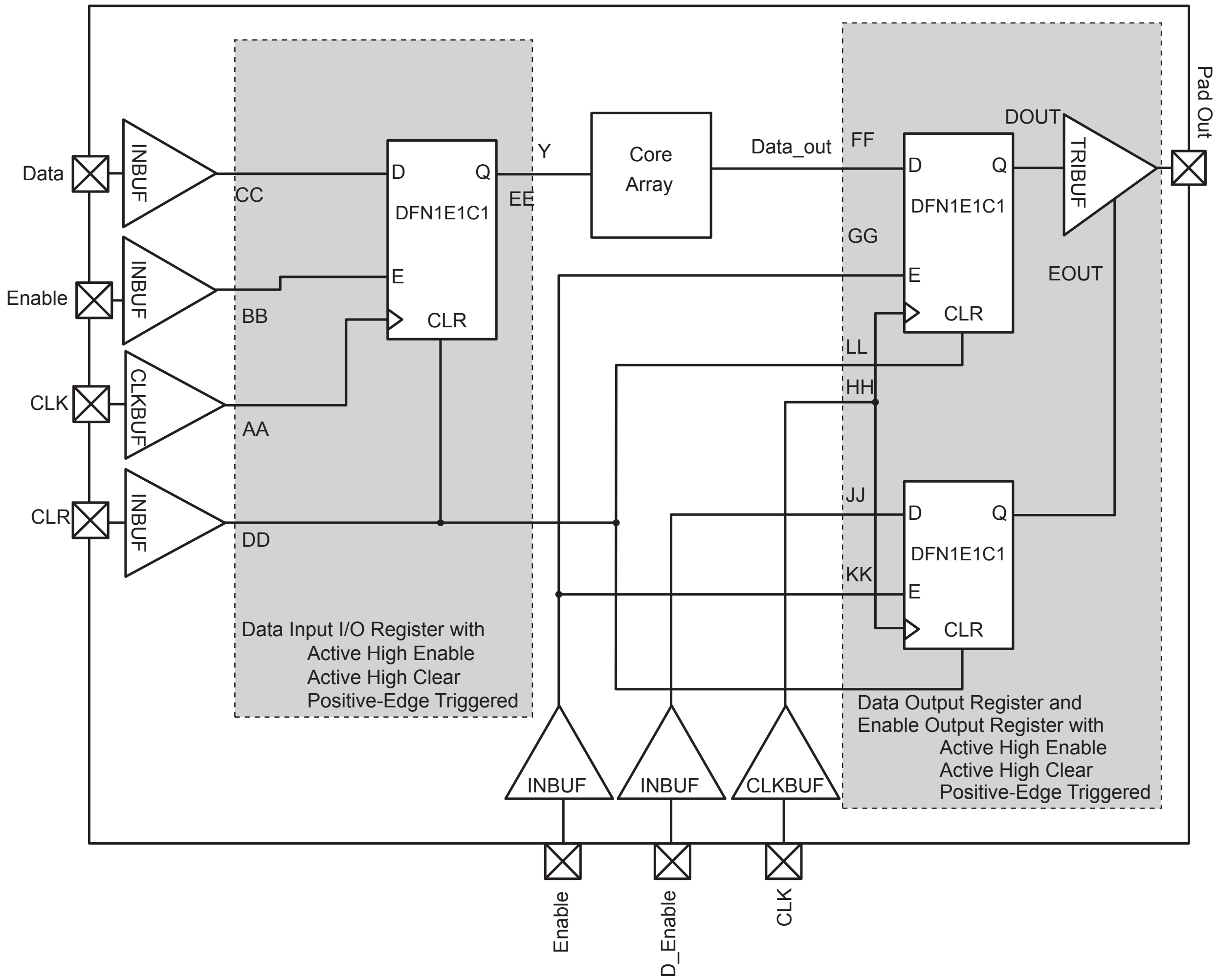

Figure 2-27 **• Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear**

VersaTile Specifications as a Sequential Module

The IGLOOe library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the *IGLOO, Fusion, and ProASIC3 Macro Library Guide*.

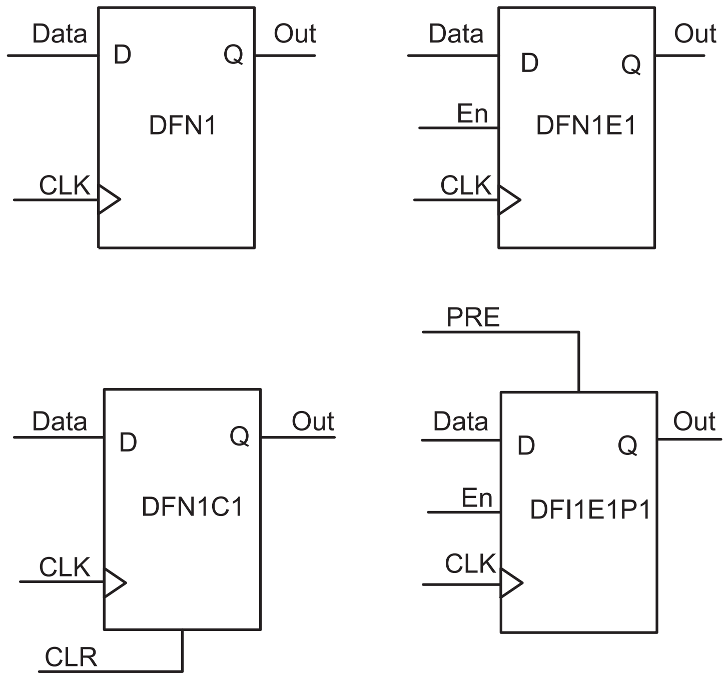

Figure 2-37 **• Sample of Sequential Cells**

Embedded SRAM and FIFO Characteristics

SRAM

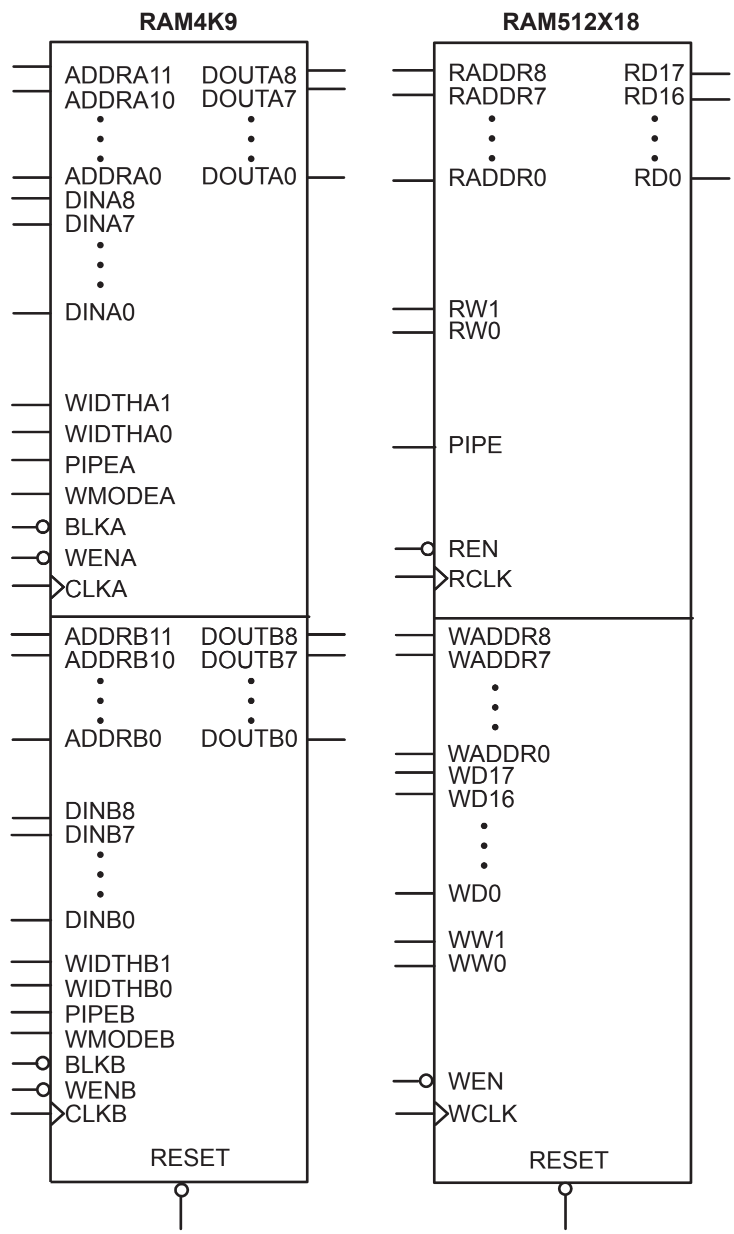

***Figure 2-41* • RAM Models**

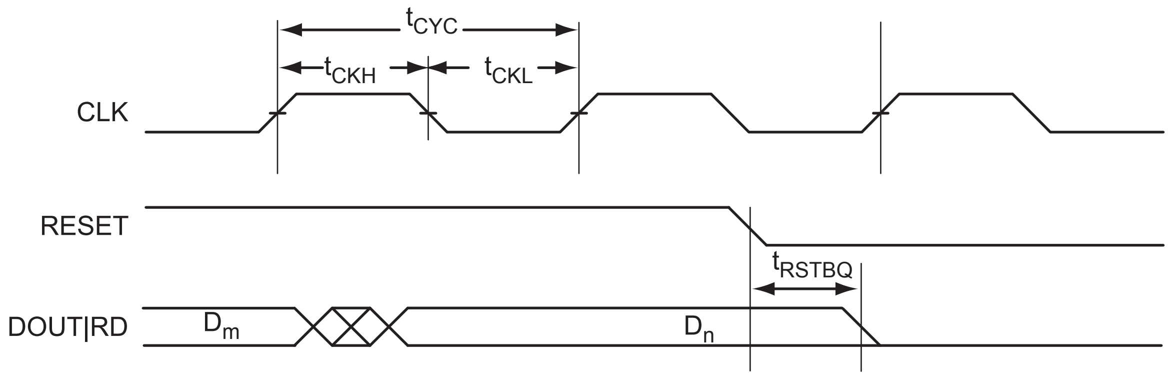

Figure 2-46 • **RAM Reset**

Applies to 1.2 V DC Core Voltage

Table 2-150 • FIFO
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.13	ns
t_{ENH}	REN, WEN Hold Time	0.31	ns
t_{BKS}	BLK Setup Time	0.47	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	1.56	ns
t_{DH}	Input Data (WD) Hold Time	0.49	ns
t_{CKQ1}	Clock HIGH to New Data Valid on RD (pass-through)	6.80	ns
t_{CKQ2}	Clock HIGH to New Data Valid on RD (pipelined)	3.62	ns
t_{RCKEF}	RCLK HIGH to Empty Flag Valid	7.23	ns
t_{WCKFF}	WCLK HIGH to Full Flag Valid	6.85	ns
t_{CKAF}	Clock HIGH to Almost Empty/Full Flag Valid	26.61	ns
t_{RSTFG}	RESET LOW to Empty/Full Flag Valid	7.12	ns
t_{RSTAF}	RESET LOW to Almost Empty/Full Flag Valid	26.33	ns
t_{RSTBQ}	RESET LOW to Data Out LOW on RD (pass-through)	4.09	ns
	RESET LOW to Data Out LOW on RD (pipelined)	4.09	ns
$t_{REMRSTB}$	RESET Removal	1.23	ns
$t_{RECRSTB}$	RESET Recovery	6.58	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	1.18	ns
t_{CYC}	Clock Cycle Time	10.90	ns
F_{MAX}	Maximum Frequency	92	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

User Pins

I/O User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to VCCI. With VCCI, VMV, and VCC supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

GL Globals

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *IGLOOe FPGA Fabric User's Guide*. All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

Refer to the I/O Structure section of the *IGLOOe FPGA Fabric User's Guide* for an explanation of the naming of global pins.

FF Flash*Freeze Mode Activation Pin

Flash*Freeze mode is available on IGLOOe devices. The FF pin is a dedicated input pin used to enter and exit Flash*Freeze mode. The FF pin is active low, has the same characteristics as a single-ended I/O, and must meet the maximum rise and fall times. When Flash*Freeze mode is not used in the design, the FF pin is available as a regular I/O. The FF pin can be configured as a Schmitt trigger input.

When Flash*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash*Freeze mode. While in Flash*Freeze mode, the Flash*Freeze pin should be constantly asserted.

The Flash*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

FG484	
Pin Number	**AGLE600 Function**
C18	GND
C19	NC
C20	NC
C21	NC
C22	VCCIB2
D1	NC
D2	NC
D3	NC
D4	GND
D5	GAA0/IO00NDB0V0
D6	GAA1/IO00PDB0V0
D7	GAB0/IO01NDB0V0
D8	IO05PDB0V0
D9	IO10PDB0V1
D10	IO12PDB0V2
D11	IO16NDB0V2
D12	IO23NDB1V0
D13	IO23PDB1V0
D14	IO28NDB1V1
D15	IO28PDB1V1
D16	GBB1/IO34PDB1V1
D17	GBA0/IO35NDB1V1
D18	GBA1/IO35PDB1V1
D19	GND
D20	NC
D21	NC
D22	NC
E1	NC
E2	NC
E3	GND
E4	GAB2/IO133PDB7V1
E5	GAA2/IO134PDB7V1
E6	GNDQ
E7	GAB1/IO01PDB0V0
E8	IO05NDB0V0

FG484	
Pin Number	**AGLE600 Function**
E9	IO10NDB0V1
E10	IO12NDB0V2
E11	IO16PDB0V2
E12	IO20NDB1V0
E13	IO24NDB1V0
E14	IO24PDB1V0
E15	GBC1/IO33PDB1V1
E16	GBB0/IO34NDB1V1
E17	GNDQ
E18	GBA2/IO36PDB2V0
E19	IO42NDB2V0
E20	GND
E21	NC
E22	NC
F1	NC
F2	IO131NDB7V1
F3	IO131PDB7V1
F4	IO133NDB7V1
F5	IO134NDB7V1
F6	VMV7
F7	VCCPLA
F8	GAC0/IO02NDB0V0
F9	GAC1/IO02PDB0V0
F10	IO15NDB0V2
F11	IO15PDB0V2
F12	IO20PDB1V0
F13	IO25NDB1V0
F14	IO27PDB1V0
F15	GBC0/IO33NDB1V1
F16	VCCPLB
F17	VMV2
F18	IO36NDB2V0
F19	IO42PDB2V0
F20	NC
F21	NC

FG484	
Pin Number	**AGLE600 Function**
F22	NC
G1	IO127NDB7V1
G2	IO127PDB7V1
G3	NC
G4	IO128PDB7V1
G5	IO129PDB7V1
G6	GAC2/IO132PDB7V1
G7	VCOMPLA
G8	GNDQ
G9	IO09NDB0V1
G10	IO09PDB0V1
G11	IO13PDB0V2
G12	IO21PDB1V0
G13	IO25PDB1V0
G14	IO27NDB1V0
G15	GNDQ
G16	VCOMPLB
G17	GBB2/IO37PDB2V0
G18	IO39PDB2V0
G19	IO39NDB2V0
G20	IO43PDB2V0
G21	IO43NDB2V0
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO128NDB7V1
H5	IO129NDB7V1
H6	IO132NDB7V1
H7	IO130PDB7V1
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO13NDB0V2
H12	IO21NDB1V0

5 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each revision of the IGLOOe datasheet.

Revision	Changes	Page
Revision 13 (December 2012)	The "IGLOOe Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43176). Also added the missing heading 'Supply Voltage' under V2.	III
	The note in Table 2-143 • IGLOOe CCC/PLL Specification and Table 2-144 • IGLOOe CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42568).	2-91, 2-92
	Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The "Security" section was modified to clarify that Microsemi does not support read-back of programmed data.	1-2
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40272).	N/A
Revision 11 (August 2012)	The drive strength, IOL, and IOH value for 3.3 V GTL and 2.5 V GTL was changed from 25 mA to 20 mA in the following tables (SAR 37180): Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels, Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings Table 2-28 • I/O Output Buffer Maximum Resistances1 Table 2-73 • Minimum and Maximum DC Input and Output Levels Table 2-77 • Minimum and Maximum DC Input and Output Levels Also added note stating "*Output drive strength is below JEDEC specification.*" for Tables 2-25, 2-26, and 2-28. Additionally, the IOL and IOH values for 3.3 V GTL+ and 2.5 V GTL+ were corrected from 51 to 35 (for 3.3 V GTL+) and from 40 to 33 (for 2.5 V GTL+) in table Table 2-21 (SAR 39713).	2-20 2-25 2-26 2-28 2-51 2-53
	In Table 2-117 • Minimum and Maximum DC Input and Output Levels, VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 37183).	2-65
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions and Packaging" section: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38318). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1